FAIRCHILD SEMICONDUCTOR®

April 2012

FDS3672

N-Channel PowerTrench® MOSFET
100V, 7.5A, 22mΩ

Features

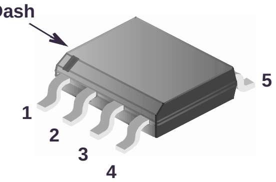
- $r_{DS(ON)}$ = 19mΩ (Typ.), V_{GS} = 10V, I_D = 7.5A
- Q_g(tot) = 28nC (Typ.), V_{GS} = 10V
- Low Miller Charge
- Low Q_{RR} Body Diode
- Optimized efficiency at high frequencies
- UIS Capability (Single Pulse and Repetitive Pulse)

Applications

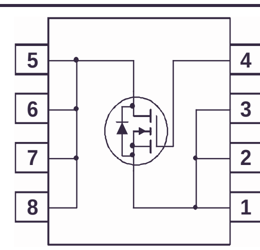
- DC/DC converters and Off-Line UPS
- Distributed Power Architectures and VRMs
- Primary Switch for 24V and 48V Systems
- High Voltage Synchronous Rectifier

Formerly developmental type 82763

Branding Dash



SO-8



MOSFET Maximum Ratings T_A = 25°C unless otherwise noted

Symbol	Parameter	Ratings	Units
V_{DSS}	Drain to Source Voltage	100	V
V_{GS}	Gate to Source Voltage	±20	V
I_D	Drain Current Continuous (T_A = 25°C, V_{GS} = 10V, $R_{\theta JA}$ = 50°C/W)	7.5	A
	Continuous (T_A = 100°C, V_{GS} = 10V, $R_{\theta JA}$ = 50°C/W)	4.8	A
	Pulsed	Figure 4	A
E_{AS}	Single Pulse Avalanche Energy (Note 1)	416	mJ
P_D	Power dissipation	2.5	W
	Derate above 25°C	20	mW/°C
T_J, T_{STG}	Operating and Storage Temperature	-55 to 150	°C

Thermal Characteristics

$R_{\theta JA}$	Thermal Resistance, Junction to Ambient at 10 seconds (Note 3)	50	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient at 1000 seconds (Note 3)	85	°C/W
$R_{\theta JC}$	Thermal Resistance, Junction to Case (Note 2)	25	°C/W

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDS3672	FDS3672	SO-8	330mm	12mm	2500 units

Electrical Characteristics T_A = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
Off Characteristics						
B_{VDSS}	Drain to Source Breakdown Voltage	I_D = 250μA, V_{GS} = 0V	100	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 80V, V_{GS} = 0V	-	-	1	μA
		V_{DS} = 80V, V_{GS} = 0V, T_C = 150°C	-	-	250	μA
I_{GSS}	Gate to Source Leakage Current	V_{GS} = ±20V	-	-	±100	nA
On Characteristics						
$V_{GS(TH)}$	Gate to Source Threshold Voltage	V_{GS} = V_{DS}, I_D = 250μA	2	-	4	V
$r_{DS(ON)}$	Drain to Source On Resistance	I_D = 7.5A, V_{GS} = 10V	-	0.019	0.023	Ω
		I_D = 6.8A, V_{GS} = 6V	-	0.023	0.028	Ω
		I_D = 7.5A, V_{GS} = 10V, T_C = 150°C	-	0.035	0.043	Ω
Dynamic Characteristics						
C_{ISS}	Input Capacitance	V_{DS} = 25V, V_{GS} = 0V, f = 1MHz	-	2015	-	pF
C_{OSS}	Output Capacitance		-	285	-	pF
C_{RSS}	Reverse Transfer Capacitance		-	70	-	pF
$Q_{g(TOT)}$	Total Gate Charge at 10V	V_{GS} = 0V to 10V; V_{DD} = 50V, I_D = 7.5A, I_g = 1.0mA	-	28	37	nC
$Q_{g(TH)}$	Threshold Gate Charge	V_{GS} = 0V to 2V; V_{DD} = 50V, I_D = 7.5A, I_g = 1.0mA	-	4	6	nC
Q_{gs}	Gate to Source Gate Charge	V_{DD} = 50V, I_D = 7.5A, I_g = 1.0mA	-	10	-	nC
Q_{gs2}	Gate Charge Threshold to Plateau		-	6.8	-	nC
Q_{gd}	Gate to Drain "Miller" Charge		-	6	-	nC
Switching Characteristics (V_{GS} = 10V)						
t_{ON}	Turn-On Time	V_{DD} = 50V, I_D = 4A, V_{GS} = 10V, R_{GS} = 10Ω	-	-	51	ns
$t_{d(ON)}$	Turn-On Delay Time		-	14	-	ns
t_r	Rise Time		-	20	-	ns
$t_{d(OFF)}$	Turn-Off Delay Time		-	37	-	ns
t_f	Fall Time		-	27	-	ns
t_{OFF}	Turn-Off Time		-	-	96	ns
Drain-Source Diode Characteristics						
V_{SD}	Source to Drain Diode Voltage	I_{SD} = 7.5A	-	-	1.25	V
		I_{SD} = 4A	-	-	1.0	V
t_{rr}	Reverse Recovery Time	I_{SD}= 7.5A, dI_{SD}/dt= 100A/μs	-	-	55	ns
Q_{RR}	Reverse Recovered Charge	I_{SD}= 7.5A, dI_{SD}/dt= 100A/μs	-	-	90	nC

Notes:
1: Starting T_J = 25°C, L = 13mH, I_{AS} = 8A.
2: $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.
3: $R_{\theta JA}$ is measured with 1.0 in^2 copper on FR-4 board

Typical Characteristics T_A = 25°C unless otherwise noted

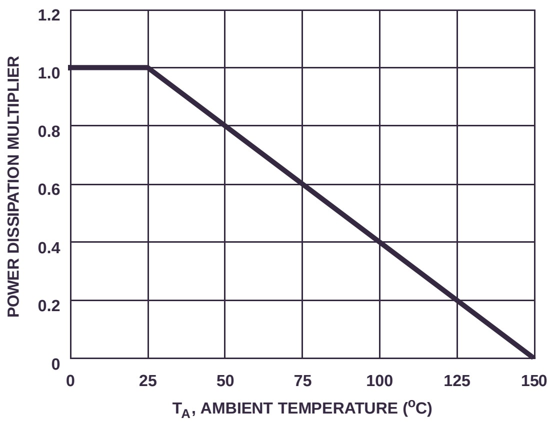


Figure 1. Normalized Power Dissipation vs Ambient Temperature

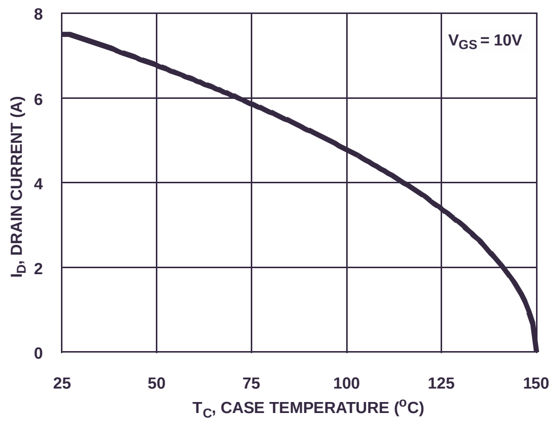


Figure 2. Maximum Continuous Drain Current vs Case Temperature

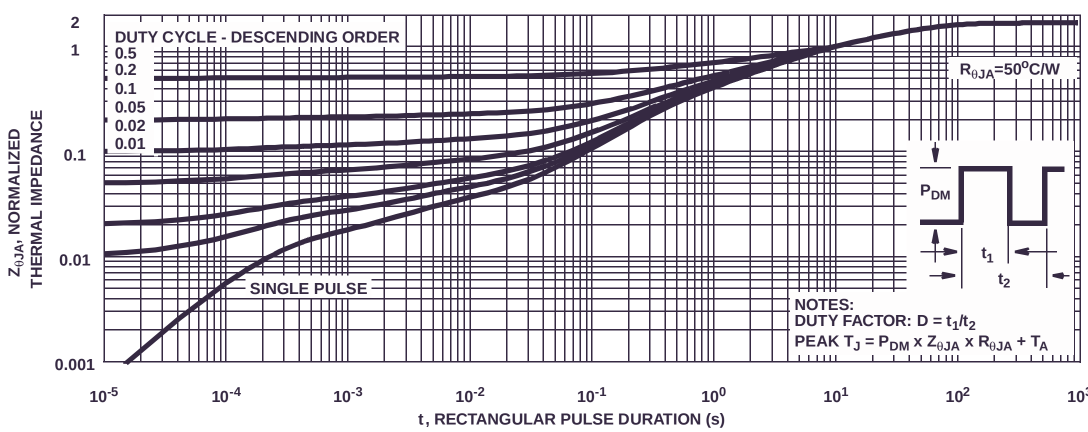


Figure 3. Normalized Maximum Transient Thermal Impedance

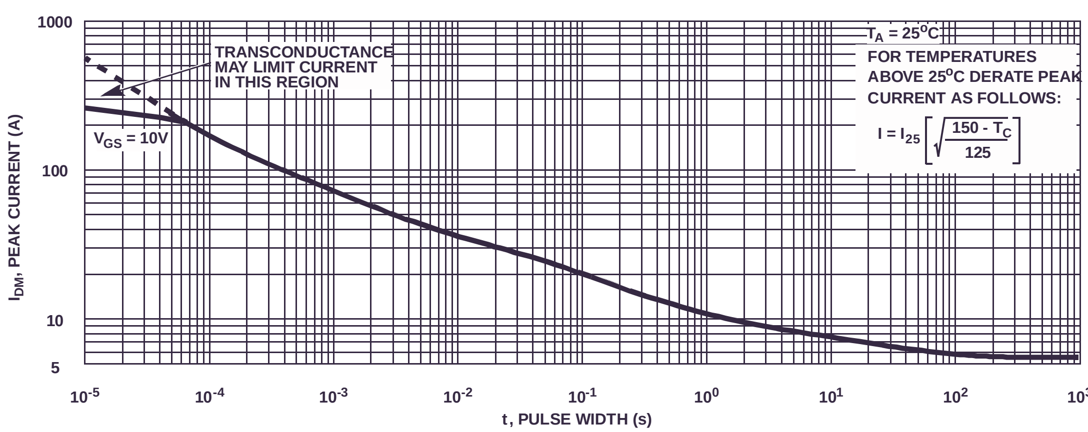


Figure 4. Peak Current Capability

Typical Characteristics T_A = 25°C unless otherwise noted

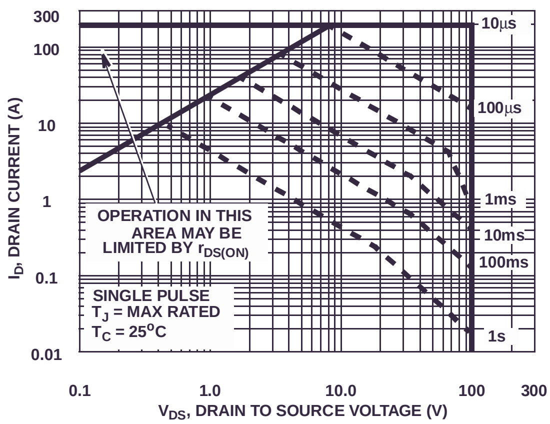


Figure 5. Forward Bias Safe Operating Area

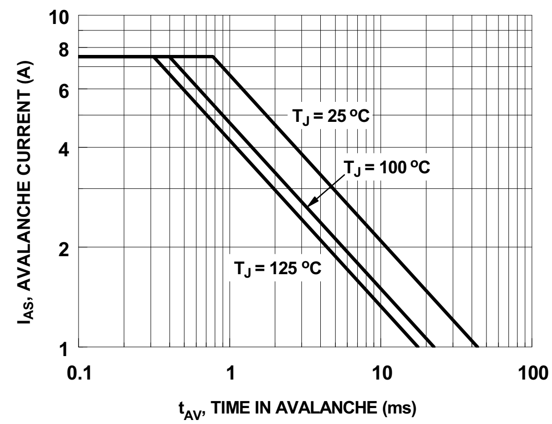


Figure 6. Unclamped Inductive Switching Capability

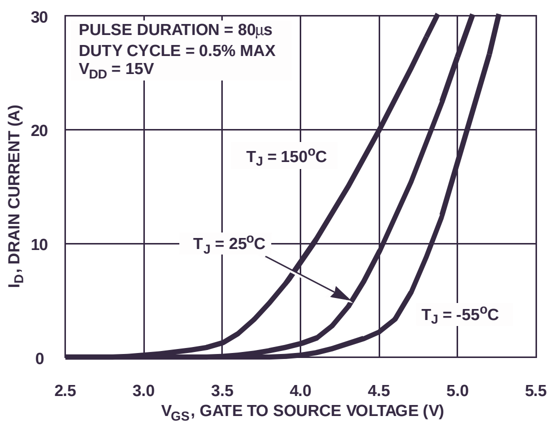


Figure 7. Transfer Characteristics

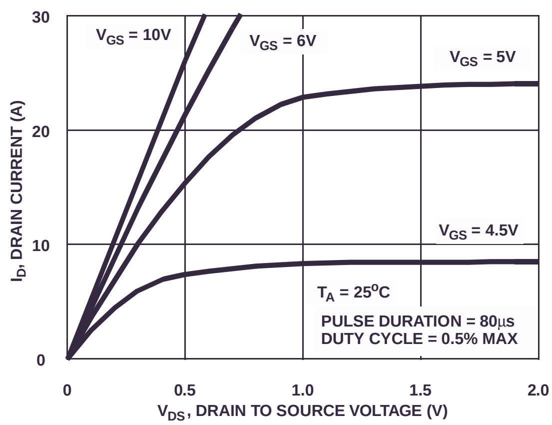


Figure 8. Saturation Characteristics

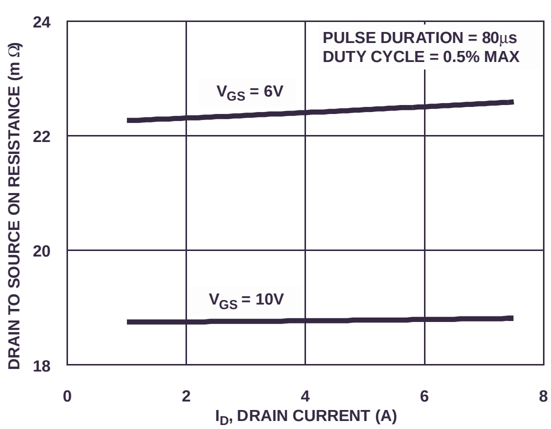


Figure 9. Drain to Source On Resistance vs Drain Current

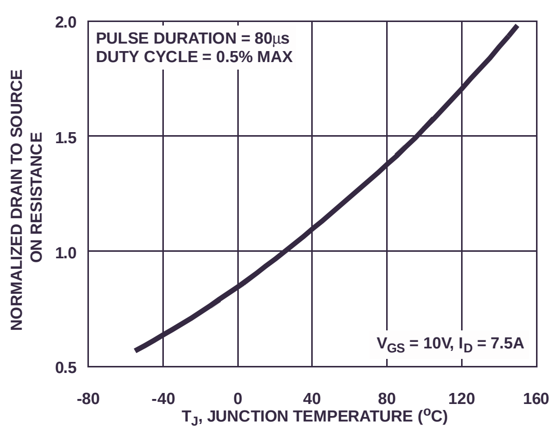


Figure 10. Normalized Drain to Source On Resistance vs Junction Temperature

Typical Characteristics T_A = 25°C unless otherwise noted

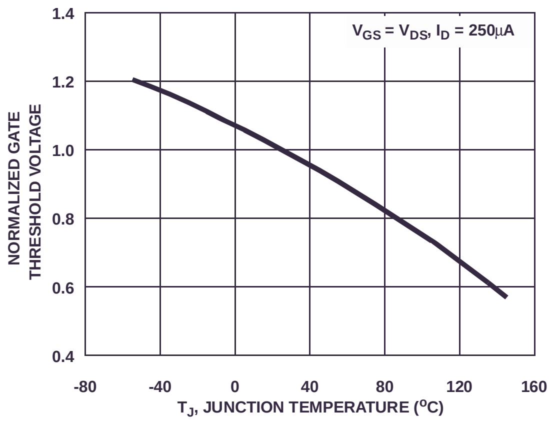


Figure 11. Normalized Gate Threshold Voltage vs Junction Temperature

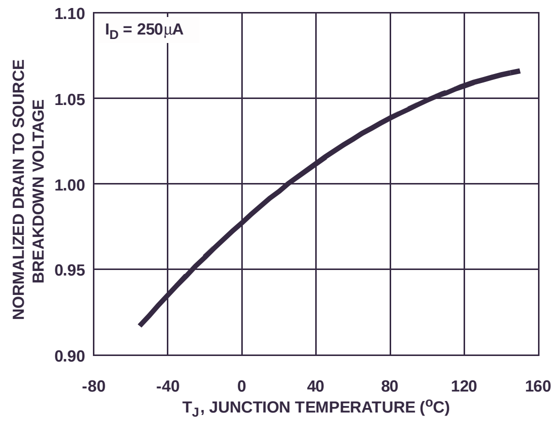


Figure 12. Normalized Drain to Source Breakdown Voltage vs Junction Temperature

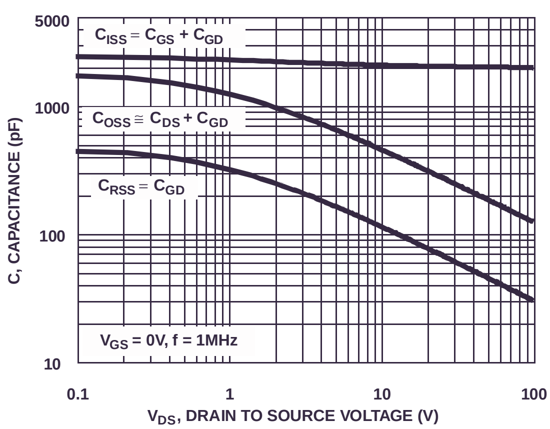


Figure 13. Capacitance vs Drain to Source Voltage

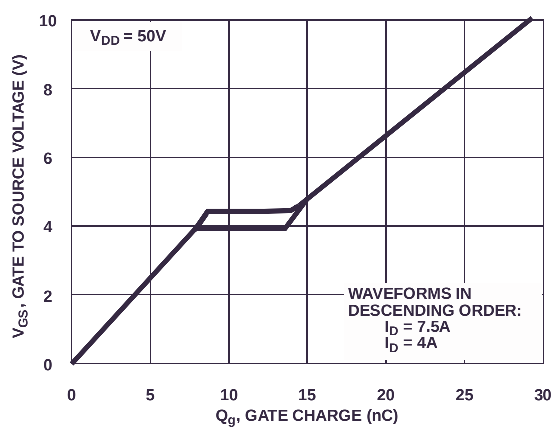


Figure 14. Gate Charge Waveforms for Constant Gate Currents

Test Circuits and Waveforms

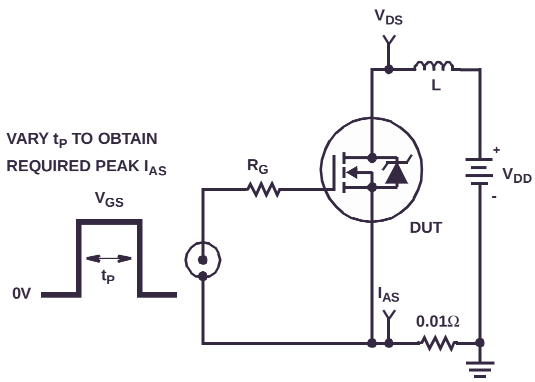


Figure 15. Unclamped Energy Test Circuit

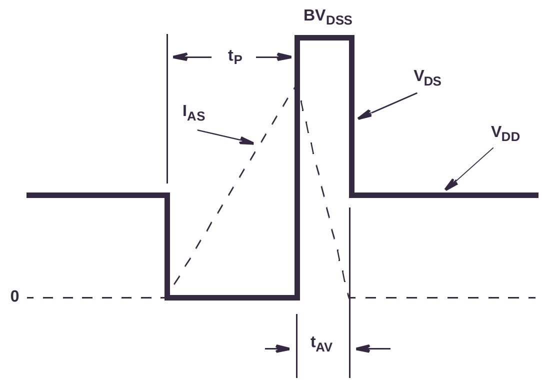


Figure 16. Unclamped Energy Waveforms

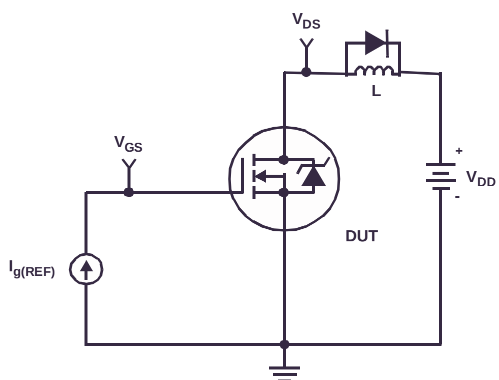


Figure 17. Gate Charge Test Circuit

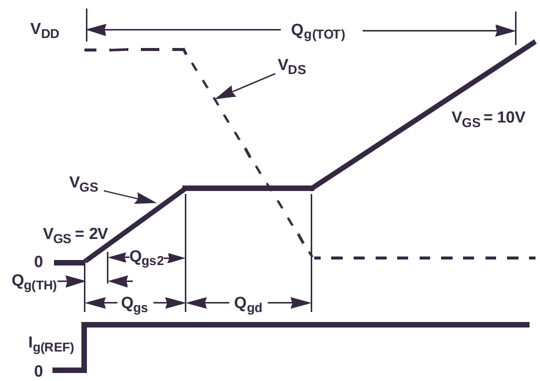


Figure 18. Gate Charge Waveforms

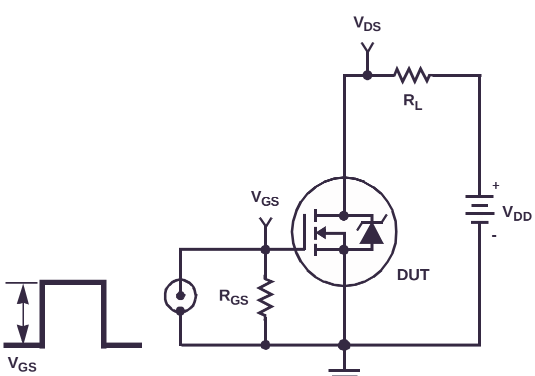


Figure 19. Switching Time Test Circuit

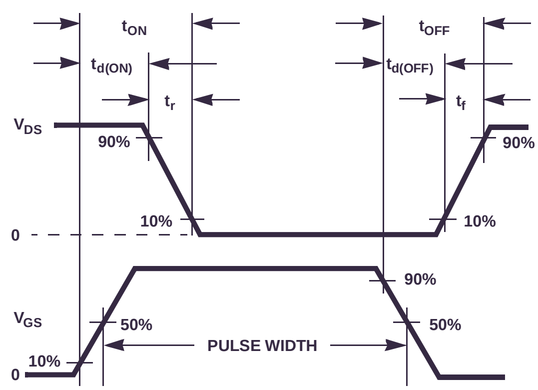


Figure 20. Switching Time Waveforms

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